

ABSTRACT OF DISCLOSURE

A method including the steps of: consecutively
5 depositing a first etch stop layer, a first compound
semiconductor and a second compound semiconductor
layer overlying a semiconductor substrate, the first etch
stop layer, the first and second compound semiconductor
layers having different compositions from one another,
10 etching the first and second compound semiconductor
layers until the etching stops at the first etch stop layer,
and forming a semiconductor laser device including the
first etch stop layer and the first and second compound
semiconductor layers. The existence of the first
15 compound semiconductor layer made of a material
different from those of the second compound
semiconductor layer and the etch stop layer enables the
etching of the second compound semiconductor layer
while controlling the etching depth thereof by using the
20 etch stop layer.

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